

## Schottky barrier diode

## RB751S-40 / RB751V-40

## ●Applications

High speed switching  
For Detection

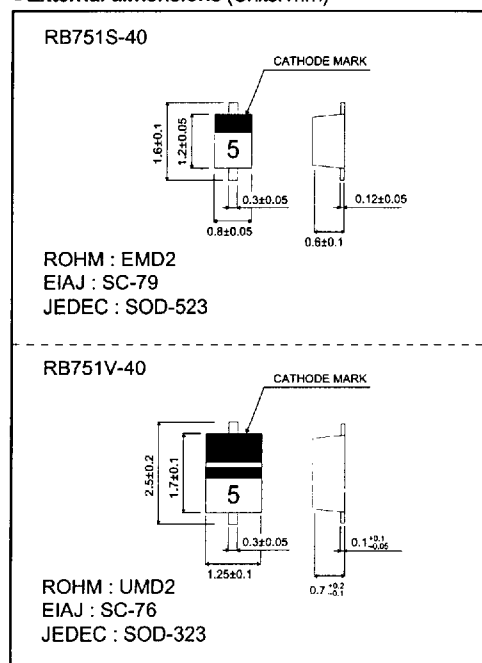
## ●Features

- 1) Small surface mounting type.
- 2) High reliability.
- 3) Low reverse current and low forward voltage.

## ●Construction

Silicon epitaxial planar

## ●External dimensions (Units: mm)



## ●Absolute maximum ratings (Ta = 25°C)

| Parameter                   | Symbol    | Limits   | Unit |
|-----------------------------|-----------|----------|------|
| Peak reverse voltage        | $V_{RM}$  | 40       | V    |
| DC reverse voltage          | $V_R$     | 30       | V    |
| Mean rectifying current     | $I_o$     | 30       | mA   |
| Peak forward surge current* | $I_{FSM}$ | 200      | mA   |
| Junction temperature        | $T_j$     | 125      | °C   |
| Storage temperature         | $T_{stg}$ | -40~+125 | °C   |

\* 60 Hz for 1 ms

## ●Electrical characteristics (Ta = 25°C)

| Parameter                     | Symbol | Min. | Typ. | Max. | Unit          | Conditions                         |
|-------------------------------|--------|------|------|------|---------------|------------------------------------|
| Forward voltage               | $V_F$  | -    | 0.26 | 0.37 | V             | $I_F = 1\text{mA}$                 |
| Reverse current               | $I_R$  | -    | 0.11 | 0.5  | $\mu\text{A}$ | $V_R = 30\text{V}$                 |
| Capacitance between terminals | $C_T$  | -    | 2.0  | -    | pF            | $V_R = 1\text{V}, f = 1\text{MHz}$ |

\* ESD sensitive product handling required.

ROHM

Diodes

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

